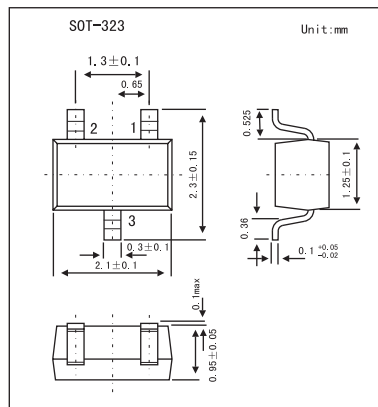


BAT854W;BAT854AW BAT854CW;BAT854SW

■ Features

- Very low forward voltage
- Very low reverse current
- Guard ring protected
- Very small SMD package.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous reverse voltage	V _R			40	V
Continuous forward current	I _F			200	mA
Repetitive peak forward current	I _{FRM}	t _p ≤ 1 s; d ≤ 0.5		300	mA
Non-repetitive peak forward current	I _{FSM}	t = 8.3 ms half sinewave; JEDEC method		1	A
Storage temperature	T _{stg}		-65	+150	°C
Junction temperature	T _j			150	°C
Operating ambient temperature	T _{amb}		-65	+150	°C
Thermal resistance from junction to ambient	R _{th j-a}			625	K/W

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Typ	Max	Unit
Forward voltage	V _F	I _F = 0.1 mA	200		mV
		I _F = 1 mA	260		
		I _F = 10 mA	340		
		I _F = 30 mA		420	
		I _F = 100 mA		550	
Continuous reverse current	I _R	V _R = 25 V; Note 1		0.5	μ A
Diode capacitance	C _d	f = 1 MHz; V _R = 1 V		20	pF

Note

1. Pulse test: t_p < 300 μ s; δ ≤ 0.02.

■ Marking

Type	BTA854W	BAT854AW	BAT854CW	BAT854SW
Marking	81	82	83	84